New 600 V IGBTs – "V Series"

Trench gate field stop – very high speed technology





Shaping a more efficient and reliable **Power Switching**

600 V IGBTs – V Series

New trench gate field stop technology – very high speed series



Energy saving

<u>Extremely low switching-off</u> combined with low conduction losses increase efficiency of high frequency converters

Power scalability

Both the **positive V**_{CE(sat)} **derating** and the linear switching losses increasing with temperature yield a <u>safer paralleling operation</u>

Robustness and reliability

Increased <u>maximum junction temperature T_{J(max)}</u> <u>up to 175 °C</u> ensures longer lifetime





life.augmented

¹⁾ on capacitive load @ V_{CC} =320V, C_{snub} =20nF





New IGBT "V" series: developed to bridge the gap between IGBTs and MOSFETs in high-frequency hard-switching applications above 20kHz





Tail-less switching-off MOSFET "like" switching-off behavior





"V" series shows the lowest *E*_{off} in the market





"V" series shows the lowest *E*_{off} in the market







Focus on main applications



Welding: double-switch forward topology









IGBT for inverter stage

- 600 V trench gate field stop
 - STGW40V60DLF
 - STGW60**V**60DLF



Solar inverters 14







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